



20V P-Channel MOSFET



SOT-23

3 69 2

Pin Definition:

- 1. Gate
- Source
 Drain

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
-20	130 @ V _{GS} =-4.5V	-2.8
	190 @ V _{GS} =-2.5V	-2.0

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

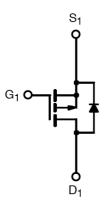
- Battery Management
- High Speed Switch

Ordering Information

Part No.	Package	Packing
TSM2301ACX RFG	SOT-23	3Kpcs / 7" Reel

Note: "G" denotes Halogen Free Product.

Block Diagram



P-Channel MOSFET

Absolute Maximum Rating (T_A=25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	-20	V	
Gate-Source Voltage		V_{GS}	±12	V	
Continuous Drain Current		I _D	-2.8	А	
Pulsed Drain Current		I _{DM}	-10	А	
Continuous Source Current (Diode Con	nduction) ^{a,b}	I _S	-1	А	
Maximum Power Dissipation	T _A =25°C	P _D	0.7	W	
	T _A =70°C		0.45		
Operating Junction Temperature		T _J	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Ambient Thermal Resistance (PCB mounted)	$R\Theta_{JA}$	175	°C/W

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on a 1 in² pad of 2oz Cu, $t \le 10$ sec.



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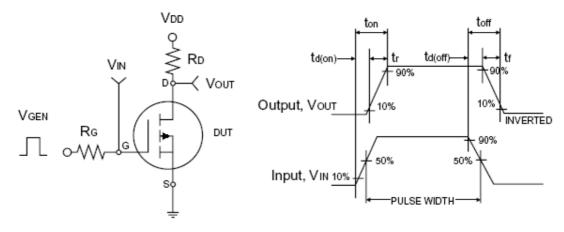


Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static	Static					
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	-20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	-0.6	-0.7	-1	V
Gate Body Leakage	$V_{GS} = \pm 12V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -20V, V_{GS} = 0V$	I _{DSS}			1.0	μΑ
Drain-Source On-State Resistance	$V_{GS} = -4.5V$, $I_D = -2.8A$			90	130	mΩ
Diam-Source On-State Resistance	$V_{GS} = -2.5V, I_D = -2.0A$	$R_{DS(ON)}$		120	190	
Diode Forward Voltage	$I_{S} = -1A, V_{GS} = 0V$	V_{SD}		-0.7	-1.3	V
Dynamic ^b						
Gate Resistance	$V_{GS} = V_{DS} = 0V$, $f=1MHz$	R_{g}		7.5		Ω
Total Gate Charge	$V_{GS} = V_{DS} = 0V$, f=1MHz $V_{DS} = -6V$, $I_{D} = -2.8A$, $V_{GS} = -4.5V$	Q_g		7.2		nC
Gate-Source Charge		Q_gs		2.2		
Gate-Drain Charge	v _{GS} = -4.5 v	Q_{gd}		1.2		
Input Capacitance	\/ 45\/ \/ 0\/	C_{iss}		480		
Output Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz	C_{oss}		460		pF
Reverse Transfer Capacitance	I = I.UIVIMZ	C_{rss}		10		
Switching ^{b.c}						
Turn-On Delay Time	V 0V D 00	t _{d(on)}		38		
Turn-On Rise Time	$V_{DD} = -6V, R_{L} = 6\Omega,$	t _r		25		20
Turn-Off Delay Time	$V_{GEN} = -4.5V,$ $R_G = 6\Omega$	t _{d(off)}		43		nS
Turn-Off Fall Time	NG = 077	t _f		5		

Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

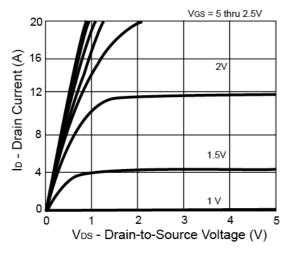


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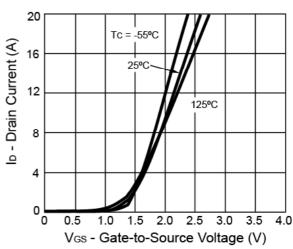


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

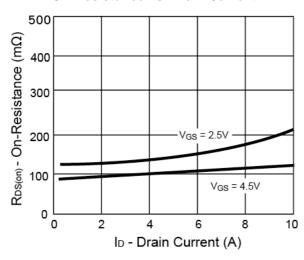
Output Characteristics



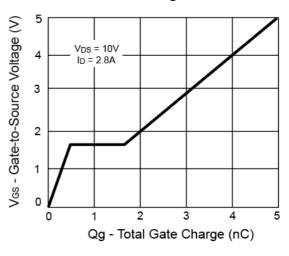
Transfer Characteristics



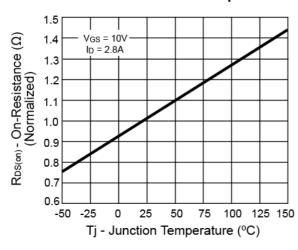
On-Resistance vs. Drain Current



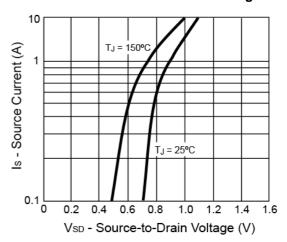
Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



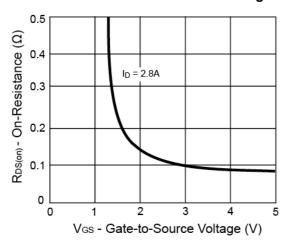


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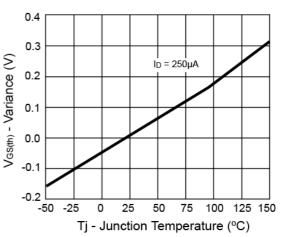


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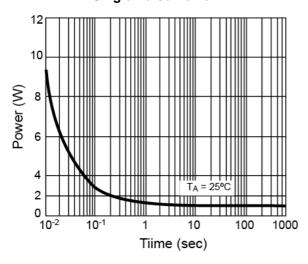
On-Resistance vs. Gate-Source Voltage



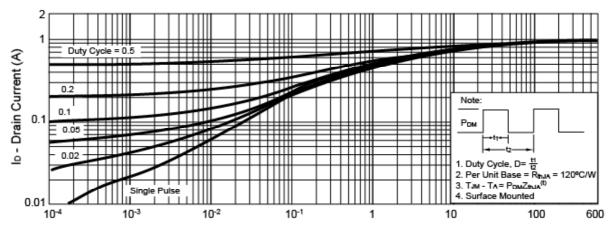
Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



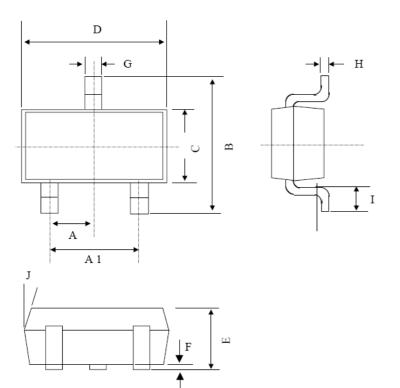
Square Wave Pulse Duration (sec)



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SOT-23 Mechanical Drawing



SOT-23 DIMENSION					
DIM	MILLIMETERS		INCHES		
DIIVI	MIN	MAX	MIN	MAX.	
Α	0.95	0.95 BSC 0.037 BS		BSC	
A1	1.9	1.9 BSC 0.074		BSC	
В	2.60	3.00	0.102	0.118	
С	1.40	1.70	0.055	0.067	
D	2.80	3.10	0.110	0.122	
Е	1.00	1.30	0.039	0.051	
F	0.00	0.10	0.000	0.004	
G	0.35	0.50	0.014	0.020	
Н	0.10	0.20	0.004	0.008	
Ī	0.30	0.60	0.012	0.024	
J	5°	10°	5°	10°	



TSM2301A 20V P-Channel MOSFET

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